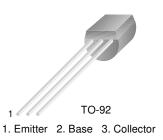


SEMICONDUCTOR®

KSC839

FM/AM RADIO RF AMP, CONV, OSC, IF AMP

- Current Gain Bandwidth Product : f_T=200MHz
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



NPN Epitaxial Silicon Transistor

Absolute Maximu	m Ratings $T_a=25^{\circ}C$ unless otherwise noted
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Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	35	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current	100	mA
P _C	Collector Power Dissipation	250	mW
ТJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

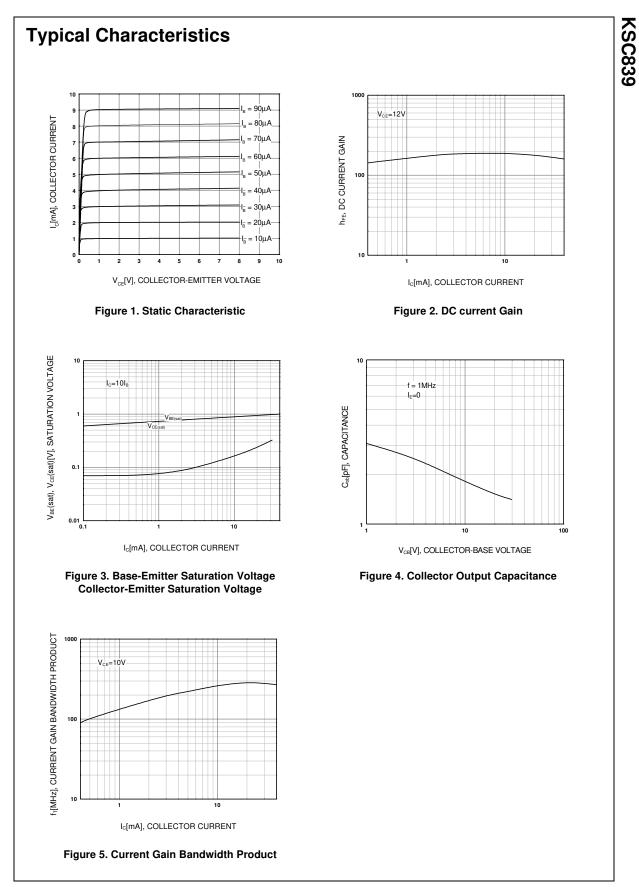
Electrical Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	35			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =5mA, I _B =0	30			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I _E =10μA, I _C =0	4			V
I _{CBO}	Collector Cut-off Current	V _{CB} =30V, I _E =0			0.1	μA
I _{EBO}	Emitter Cut-off Current	$V_{EB}=4V, I_{C}=0$			0.1	μA
h _{FE}	DC Current Gain	V _{CE} =12V, I _C =2mA	40		400	
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =6V, I _C =1mA	0.65	0.70	0.75	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA		0.1	0.4	V
f _T	Current Gain Bandwidth Product	V _{CE} =10V, I _C =1mA	80	200		MHz
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz		2.0	3.5	pF

h_{FE} Classification

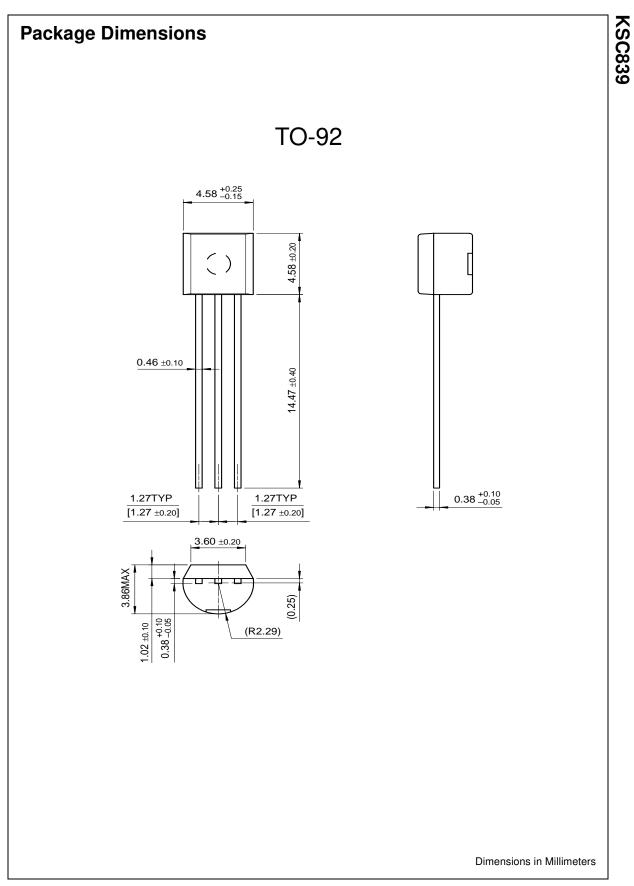
Classification	R	0	Y	G
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400

KSC839



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.